



3N90

Power MOSFET

3.0A, 900V N-CHANNEL POWER MOSFET

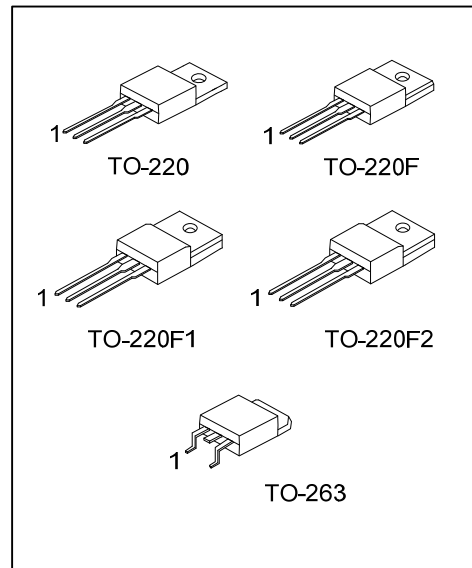
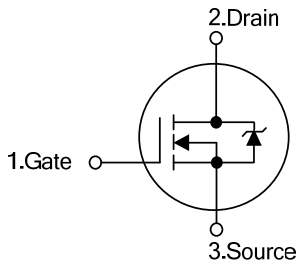
■ DESCRIPTION

The UTC **3N90** provides excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

- * $R_{DS(ON)} \leq 3.5 \Omega @ V_{GS}=10V, I_D=1.5A$
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

■ SYMBOL



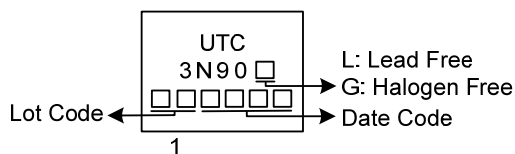
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
3N90L-TA3-T	3N90G-TA3-T	TO-220	G	D	S	Tube
3N90L-TF3-T	3N90G-TF3-T	TO-220F	G	D	S	Tube
3N90L-TF1-T	3N90G-TF1-T	TO-220F1	G	D	S	Tube
3N90L-TF2-T	3N90G-TF2-T	TO-220F2	G	D	S	Tube
3N90L-TQ2-T	3N90G-TQ2-T	TO-263	G	D	S	Tube
3N90L-TQ2-R	3N90G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>3N90G-TA3-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1 TF2: TO-220F2, TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	3	A
	Pulsed (Note 2)	I_{DM}	12	A
Avalanche Energy		E_{AS}	195	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	1.85	V/ns
Power Dissipation	TO-220/TO-263	P_D	90	W
	TO-220F/TO-220F1		36	W
	TO-220F2		37	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=30\text{mH}$, $I_{AS}=3.6\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 4.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220/ TO-263	θ_{JC}	1.38	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		3.47	
	TO-220F2		3.37	

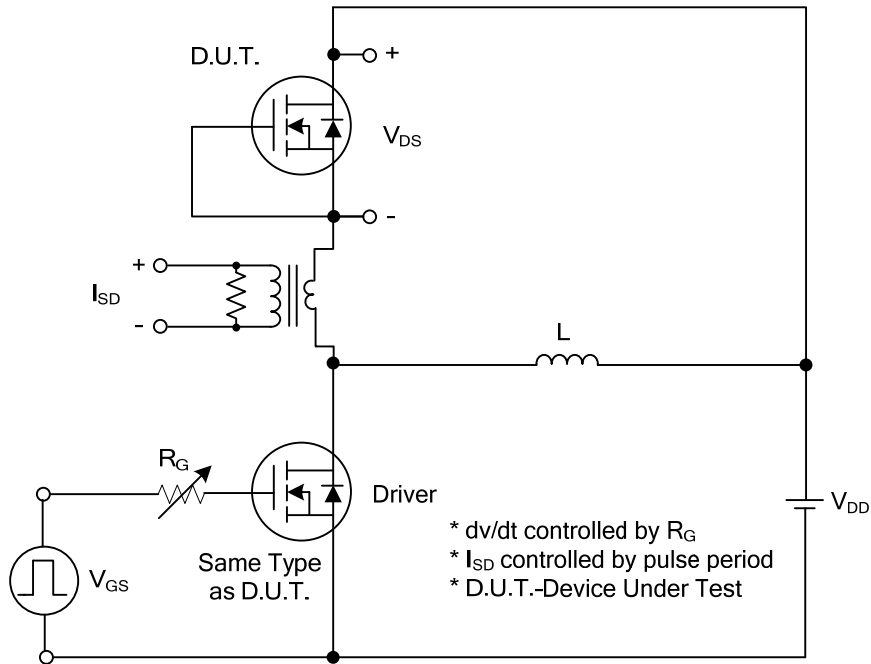
■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	900			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=900V, V_{GS}=0V$			10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$			± 10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3.0		5.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1.5A$			3.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$		850		pF
Output Capacitance	C_{OSS}			95		pF
Reverse Transfer Capacitance	C_{RSS}			10		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=100V, V_{GS}=10V, I_D=4A$ $I_G=1\text{mA}$ (Note 1, 2)		27		nC
Gate-Source Charge	Q_{GS}			10		nC
Gate-Drain Charge	Q_{GD}			7.8		nC
Turn-On Delay Time (Note 1)	$t_{D(ON)}$	$V_{DD}=100V, V_{GS}=10V, I_D=4A,$ $R_G=25\Omega$ (Note 1, 2)		14		ns
Turn-On Rise Time	t_R			17		ns
Turn-Off Delay Time	$t_{D(OFF)}$			70		ns
Turn-Off Fall Time	t_F			48		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				3	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				12	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=3.0A, V_{GS}=0V$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	$I_S=4.0A, V_{GS}=0V,$ $di_F/dt=100A/\mu s$		461		ns
Body Diode Reverse Recovery Charge	Q_{rr}				9.2	

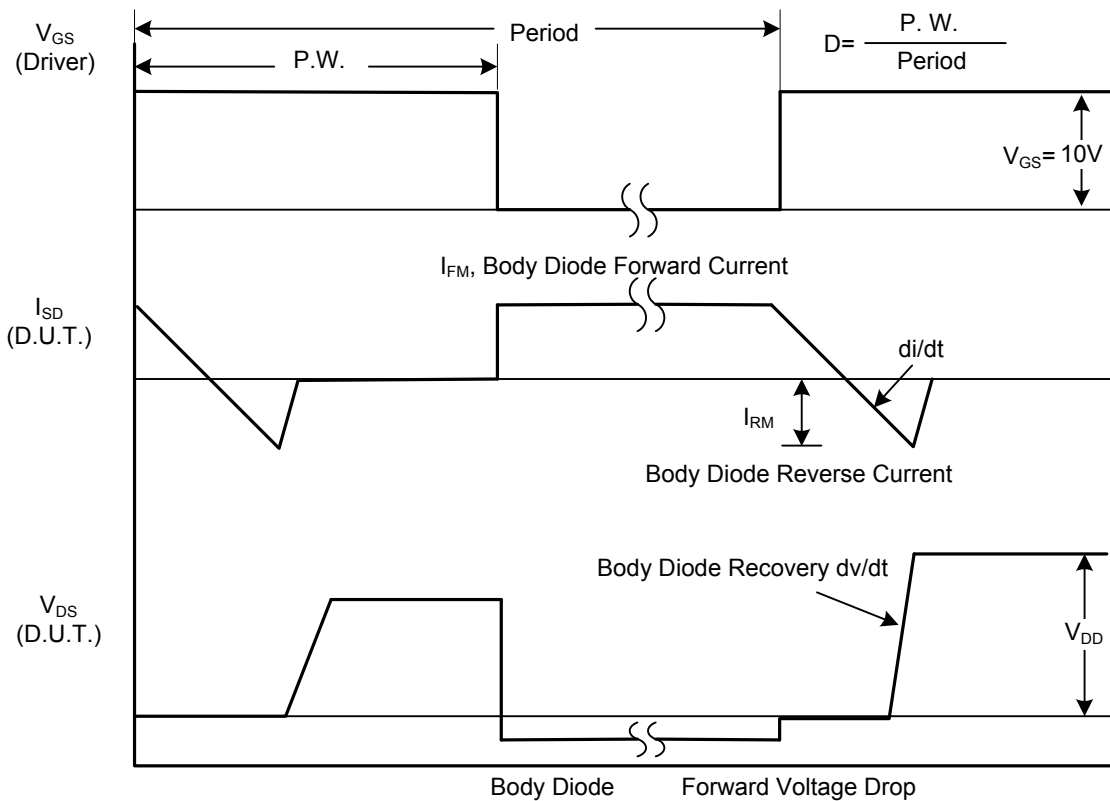
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



Peak Diode Recovery dv/dt Test Circuit



Peak Diode Recovery dv/dt Waveforms

TEST CIRCUITS AND WAVEFORMS

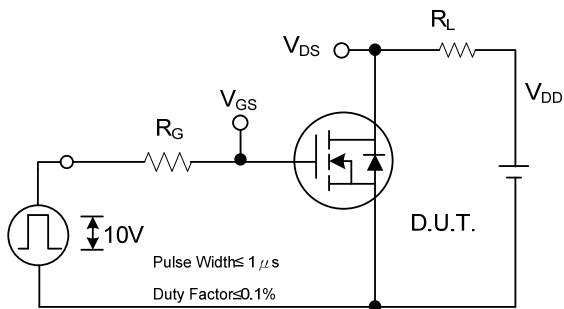


Fig. 2A Switching Test Circuit

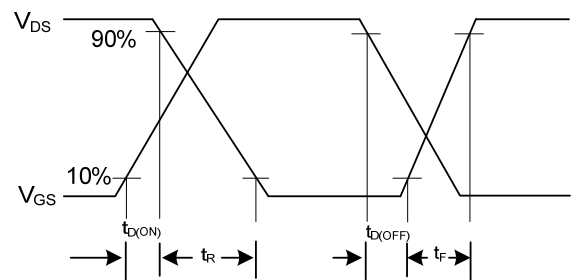


Fig. 2B Switching Waveforms

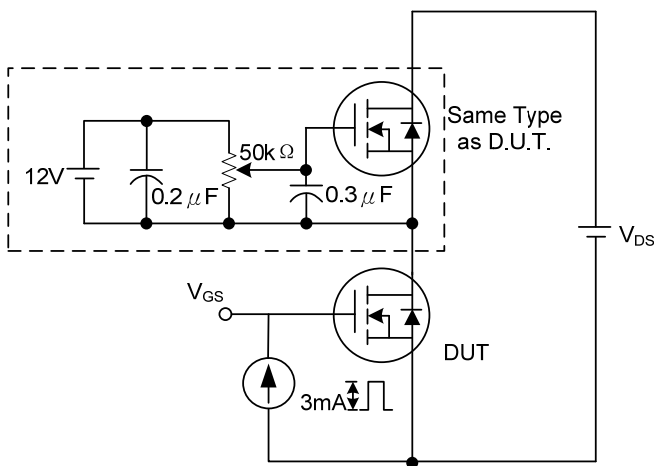


Fig. 3A Gate Charge Test Circuit

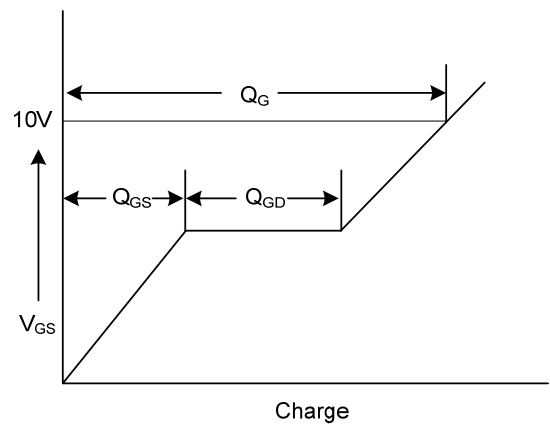


Fig. 3B Gate Charge Waveform

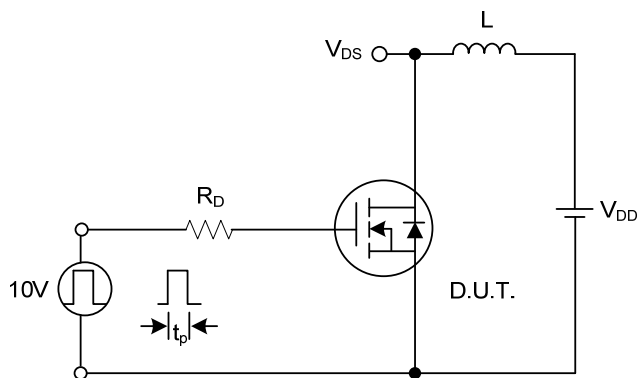


Fig. 4A Unclamped Inductive Switching Test Circuit

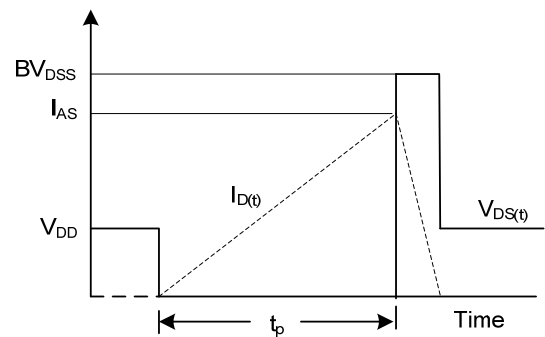
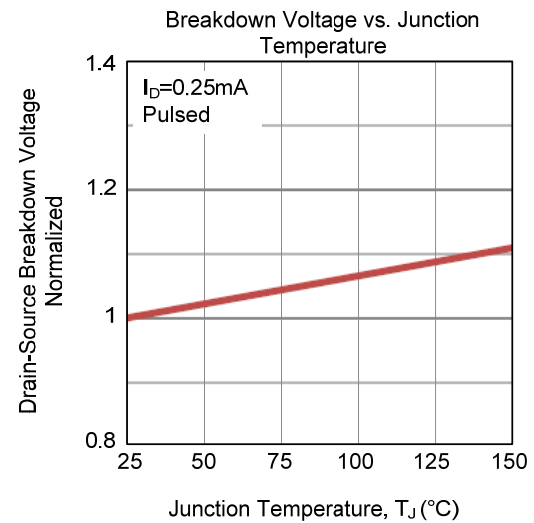
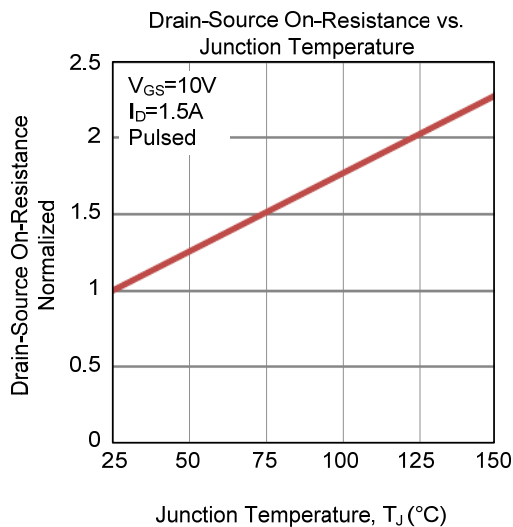
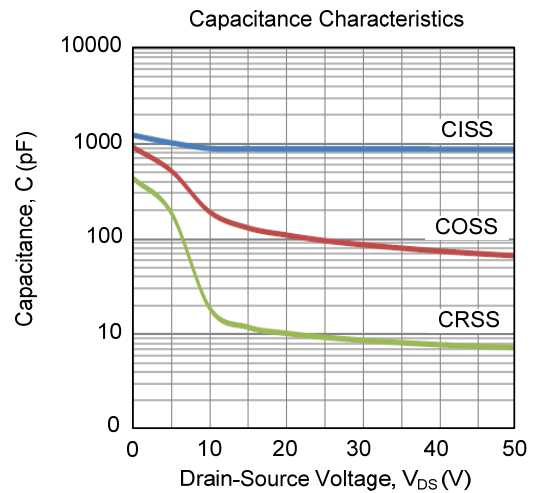
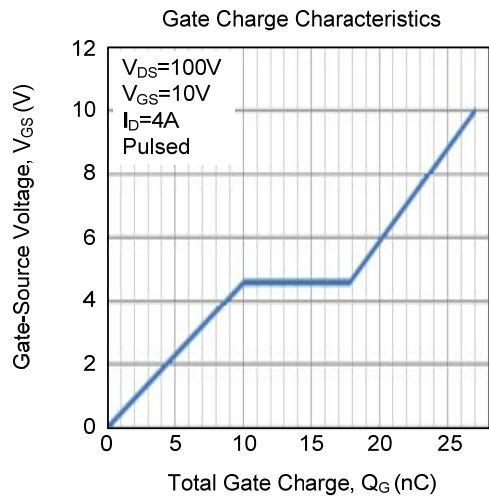
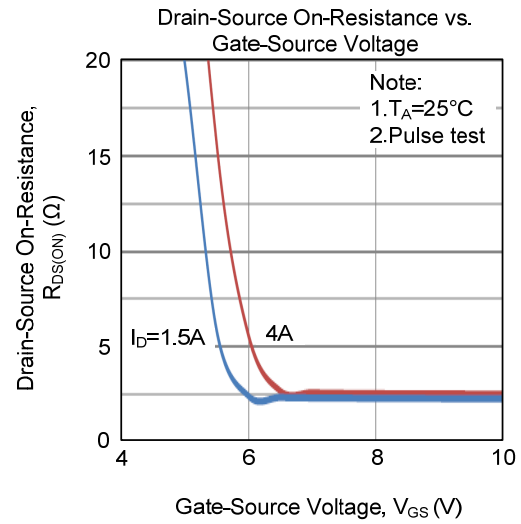
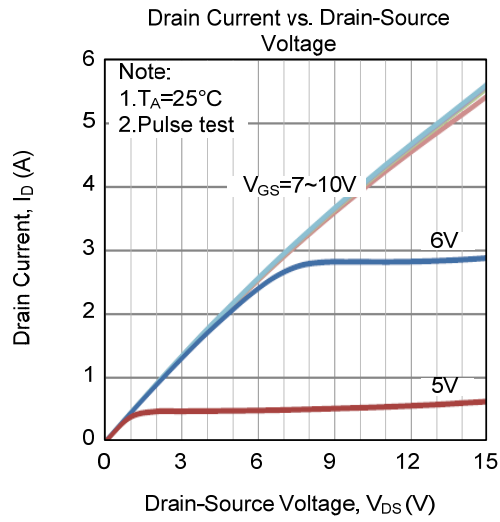
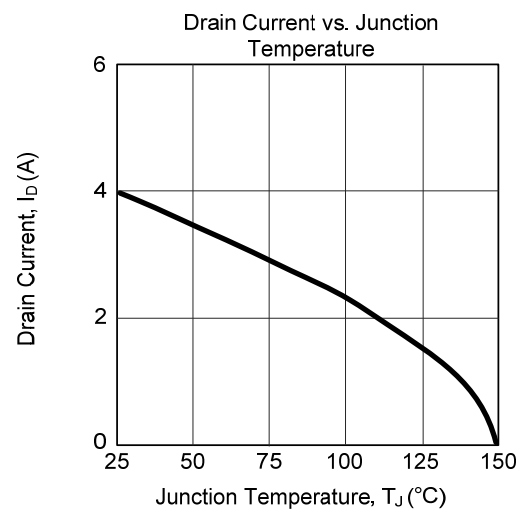
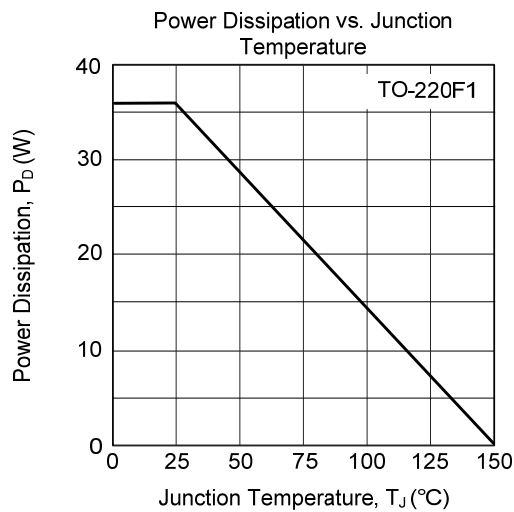
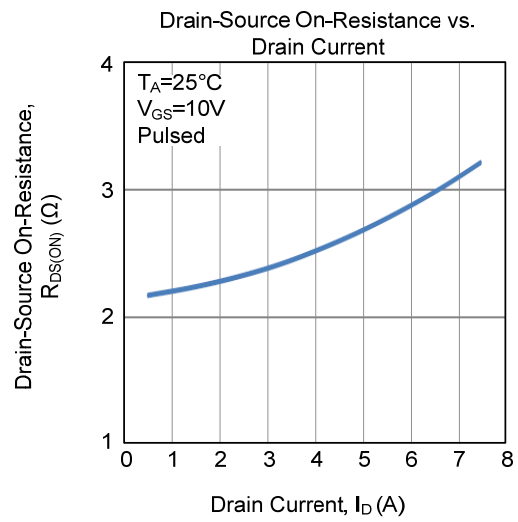
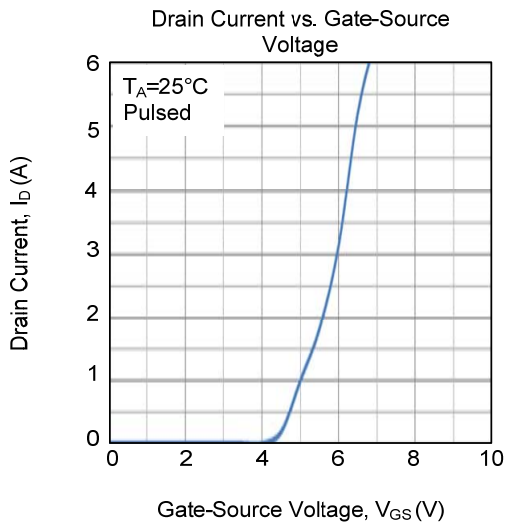
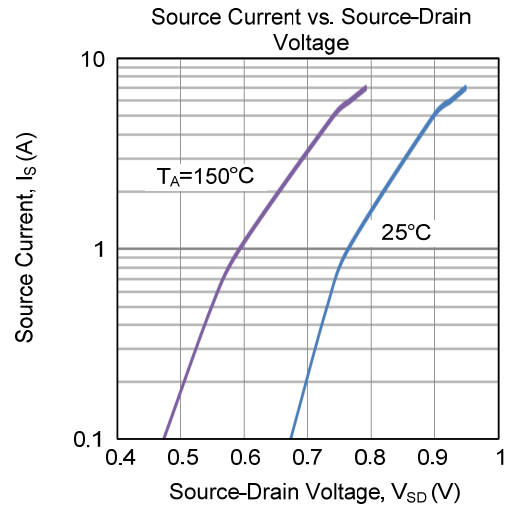
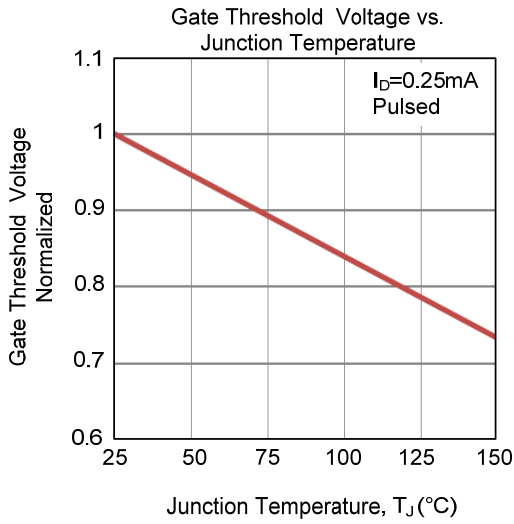


Fig. 4B Unclamped Inductive Switching Waveforms

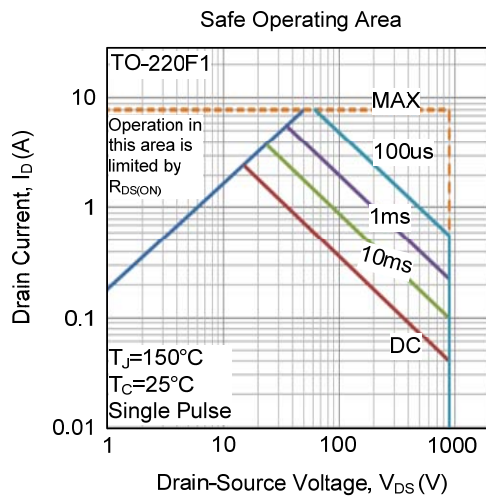
TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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